

IN THE CLAIMS

Please add new claims 22-25 as follows:

22. A method of forming a cantilever probe contactor, the method comprising:
successively patterning a first and second sacrificial layer of resist over a substrate,
each layer of resist having an opening;
depositing a first conductive material after patterning the first sacrificial layer,
depositing a second conductive material after patterning the second sacrificial layer to
form a cantilever element having:
a first portion formed in an opening in the first sacrificial layer, and
a second portion comprising a support element coupled to the first portion and
formed in an opening in the second sacrificial layer;
and
removing the first and second sacrificial layers simultaneously.

23. A method of forming a cantilever probe contactor, the method comprising:
successively patterning a first and second sacrificial layer of resist over a substrate,
each layer of resist having an opening;
depositing a first conductive material after patterning the first sacrificial layer;
depositing a second conductive material after patterning the second sacrificial layer to
form a cantilever element having:
a first portion formed in an opening in the first sacrificial layer,
a second portion comprising a support element coupled to the first portion and
formed in an opening in the second sacrificial layer, and

a third portion comprising a contact element coupled to the first portion, at least a part of the third portion being formed in the substrate;

and

removing the first and second sacrificial layers simultaneously,

wherein the contact element is formed of a conductive material in a predetermined opening formed in the substrate.

24. The method of claim 23, wherein the substrate is a silicon substrate.

25. The method of claim 22, wherein the conductive material includes at least nickel.